

*CLAIM AMENDMENTS*

1. (Currently Amended) A semiconductor device having a pad region and a circuit region, comprising:

a low-k dielectric film ~~formed~~ on a pad region and a circuit region of a substrate, the low-k dielectric film having dielectric constant of no more than 3 or less;

an insulating film ~~formed in on~~ the low-k dielectric film of the pad region, the insulating film having higher strength than the low-k dielectric film;

multi-layer wirings ~~formed in on~~ the insulating film of the pad region and ~~in on~~ the low-k dielectric film of the circuit region; and

a bonding pad ~~formed on a highest an outermost~~ wiring of the multi-layer wirings of the pad region.

2. (Currently Amended) The semiconductor device according to claim 1, wherein sidewalls of the wiring ~~formed~~ in the pad region are surrounded by the ~~insulating~~ insulating film.

3. (Currently Amended) The semiconductor device according to claim 1, wherein the low-k dielectric film is an insulating film containing silicon, carbon, oxygen, and hydrogen, ~~or a polymer film containing hydrogen and carbon~~.

4. (Currently Amended) A semiconductor device having a pad region and a circuit region, comprising:

multi-layer low-k dielectric films ~~formed~~ on a pad region and a circuit region of a substrate, each of the multi-layer low-k dielectric films having a dielectric constant of no more than 3 or less;

insulating films ~~formed in on~~ each of the multi-layer low-k dielectric films of the pad region, each of the insulating films having higher strength than the low-k dielectric film;

wirings ~~formed in on~~ each of the insulating films of the pad region and ~~in on~~ each of the low-k dielectric films of the circuit region; and

a bonding pad ~~formed on a highest an outermost~~ wiring of the wirings of the pad region.

5. (Currently Amended) The semiconductor device according to claim 4, wherein sidewalls of the wirings ~~formed~~ in the pad region are surrounded by the ~~insulating insulating~~ films.

6. (Currently Amended) A method for manufacturing a semiconductor device having a pad region and a circuit region, comprising:

forming a low-k dielectric film on an entire surface of a substrate, the low-k dielectric film having dielectric constant of no more than 3 or less;

forming an opening in the low-k dielectric film of the pad region;

forming a first insulating film having higher strength than the low-k dielectric film in the opening; and

forming wirings ~~in~~ on the first insulating film of the pad region and ~~in~~ on the low-k dielectric film of the circuit region using a damascene process.

7. (Currently Amended) The manufacturing method according to claim 6, wherein the forming an opening includes:

forming a second insulating film on the low-k dielectric film;

forming a resist pattern on the second insulating film; and

patterning the second insulating film and the low-k dielectric film using the resist pattern as mask, ~~and~~ wherein the first insulating film ~~is formed so that has a surface of the first insulating film is higher further from the substrate than a surface of the low-k dielectric film and is lower closer to the substrate~~ than a surface of the low-k dielectric film and ~~is lower closer to the substrate~~ than a surface of the resist pattern.

8. (Currently Amended) The manufacturing method according to claim 6, wherein, in the forming ~~the~~ a first insulating film, ~~forming a silicon oxide film is formed using a by liquid-phase deposition method~~.

9. (Currently Amended) The manufacturing method according to claim 6, including forming the multi-layer wirings are formed by repeating the repeatedly forming a low-k dielectric film, forming an opening, forming a first insulating film, and forming wirings, and ~~wherein forming a bonding pad is formed on a highest wiring of the multi-layer wirings of the pad region most distant from the substrate~~.

10. (New) The semiconductor device according to claim 1, wherein the low-k dielectric film is a polymer film containing hydrogen and carbon.